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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	154
Number of Gates	1000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-55°C ~ 125°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3p1000-pq208m

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that this net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100% because all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
  - Bit 0 (LSB) = 100%
  - Bit 1 = 50%
  - Bit 2 = 25%
  - …
  - Bit 7 (MSB) = 0.78125%
  - Average toggle rate = (100% + 50% + 25% + 12.5% + . . . + 0.78125%) / 8

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

Table 2-23 • **Toggle Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

Table 2-24 • **Enable Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%

1.5 V DC Core Voltage

Table 2-52 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew
Military-Case Conditions: T_J = 125°C, VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.61	5.90	0.04	1.45	2.09	0.40	5.98	4.73	2.52	2.24	7.45	6.19	ns
	–1	0.52	5.02	0.03	1.23	1.78	0.34	5.09	4.02	2.15	1.90	6.34	5.27	ns
8 mA	Std.	0.61	4.80	0.04	1.45	2.09	0.40	4.86	4.02	2.87	2.85	6.32	5.49	ns
	–1	0.52	4.08	0.03	1.23	1.78	0.34	4.13	3.42	2.44	2.43	5.38	4.67	ns
12 mA	Std.	0.61	4.02	0.04	1.45	2.09	0.40	4.06	3.49	3.09	3.23	5.53	4.96	ns
	–1	0.52	3.42	0.03	1.23	1.78	0.34	3.46	2.97	2.63	2.75	4.70	4.22	ns
16 mA	Std.	0.61	3.79	0.04	1.45	2.09	0.40	3.84	3.38	3.14	3.34	5.30	4.84	ns
	–1	0.52	3.23	0.03	1.23	1.78	0.34	3.26	2.87	2.67	2.84	4.51	4.12	ns
24 mA	Std.	0.61	3.67	0.04	1.45	2.09	0.40	3.72	3.39	3.20	3.74	5.18	4.86	ns
	–1	0.52	3.13	0.03	1.23	1.78	0.34	3.16	2.88	2.72	3.18	4.41	4.13	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-53 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Military-Case Conditions: T_J = 125°C, VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.61	3.26	0.04	1.45	2.09	0.40	3.30	2.48	2.52	2.38	4.76	3.95	ns
	–1	0.52	2.77	0.03	1.23	1.78	0.34	2.80	2.11	2.15	2.03	4.05	3.36	ns
8 mA	Std.	0.61	2.66	0.04	1.45	2.09	0.40	2.68	1.97	2.87	3.00	4.15	3.43	ns
	–1	0.52	2.26	0.03	1.23	1.78	0.34	2.28	1.67	2.44	2.55	3.53	2.92	ns
12 mA	Std.	0.61	2.32	0.04	1.45	2.09	0.40	2.33	1.72	3.09	3.40	3.80	3.18	ns
	–1	0.52	1.97	0.03	1.23	1.78	0.34	1.99	1.46	2.63	2.89	3.23	2.71	ns
16 mA	Std.	0.61	2.26	0.04	1.45	2.09	0.40	2.28	1.67	3.15	3.51	3.74	3.14	ns
	–1	0.52	1.92	0.03	1.23	1.78	0.34	1.94	1.42	2.68	2.98	3.18	2.67	ns
24 mA	Std.	0.61	2.28	0.04	1.45	2.09	0.40	2.30	1.61	3.21	3.90	3.77	3.07	ns
	–1	0.52	1.94	0.03	1.23	1.78	0.34	1.96	1.37	2.73	3.32	3.20	2.61	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-56 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew
Military-Case Conditions: T_J = 125°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.63	5.64	0.05	1.10	0.45	5.74	4.78	2.50	2.43	8.20	7.24	ns
	–1	0.54	4.79	0.04	0.94	0.39	4.88	4.06	2.13	2.07	6.98	6.16	ns
6 mA	Std.	0.63	4.64	0.05	1.10	0.45	4.73	4.16	2.84	3.01	7.19	6.62	ns
	–1	0.54	3.95	0.04	0.94	0.39	4.02	3.54	2.42	2.56	6.11	5.63	ns
8 mA	Std.	0.63	4.64	0.05	1.10	0.45	4.73	4.16	2.84	3.01	7.19	6.62	ns
	–1	0.54	3.95	0.04	0.94	0.39	4.02	3.54	2.42	2.56	6.11	5.63	ns
12 mA	Std.	0.63	3.94	0.05	1.10	0.45	4.01	3.67	3.07	3.39	6.47	6.13	ns
	–1	0.54	3.35	0.04	0.94	0.39	3.41	3.12	2.61	2.88	5.51	5.21	ns
16 mA	Std.	0.63	3.94	0.05	1.10	0.45	4.01	3.67	3.07	3.39	6.47	6.13	ns
	–1	0.54	3.35	0.04	0.94	0.39	3.41	3.12	2.61	2.88	5.51	5.21	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

Table 2-57 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Military-Case Conditions: T_J = 125°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.63	3.07	0.05	1.10	0.45	3.13	2.46	2.50	2.57	5.59	4.91	ns
	–1	0.54	2.61	0.04	0.94	0.39	2.66	2.09	2.13	2.19	4.75	4.18	ns
6 mA	Std.	0.63	2.51	0.05	1.10	0.45	2.55	1.97	2.84	3.16	5.01	4.43	ns
	–1	0.54	2.13	0.04	0.94	0.39	2.17	1.67	2.41	2.69	4.26	3.76	ns
8 mA	Std.	0.63	2.51	0.05	1.10	0.45	2.55	1.97	2.84	3.16	5.01	4.43	ns
	–1	0.54	2.13	0.04	0.94	0.39	2.17	1.67	2.41	2.69	4.26	3.76	ns
12 mA	Std.	0.63	2.24	0.05	1.10	0.45	2.28	1.72	3.07	3.54	4.74	4.18	ns
	–1	0.54	1.90	0.04	0.94	0.39	1.94	1.47	2.61	3.01	4.03	3.56	ns
16 mA	Std.	0.63	2.24	0.05	1.10	0.45	2.28	1.72	3.07	3.54	4.74	4.18	ns
	–1	0.54	1.90	0.04	0.94	0.39	1.94	1.47	2.61	3.01	4.03	3.56	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.*

3.3 V LVCMOS Wide Range

Table 2-58 • Minimum and Maximum DC Input and Output Levels Applicable to Pro I/O Banks for A3PE600L and A3PE3000L Only

3.3 V LVCMOS Wide Range	Equiv. Software Default Drive Strength Option[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength		Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	µA	µA	Max. mA[4]	Max. mA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	25	27	15	15
100 µA	4 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	25	27	15	15
100 µA	6 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	51	54	15	15
100 µA	12 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	103	109	15	15
100 µA	16 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	132	127	15	15
100 µA	24 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	268	181	15	15

Notes:

1. *Note that 3.3 V LVCMOS wide range is applicable to 100 µA drive strength only. The configuration will not operate at the equivalent software default drive strength. These values are for normal ranges only.*
2. *I_{IL} is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *I_{IH} is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
4. *Currents are measured at 125°C junction temperature.*
5. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-A specification.*
6. *Software default selection highlighted in gray.*

Table 2-59 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks

3.3 V LVCMOS Wide Range	Equiv. Software Default Drive Strength Option[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength		Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	µA	µA	Max. mA[4]	Max. mA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	25	27	15	15
100 µA	4 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	25	27	15	15
100 µA	6 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	51	54	15	15
100 µA	8 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	51	54	15	15
100 µA	12 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	103	109	15	15
100 µA	16 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	132	127	15	15

Notes:

1. *Note that 3.3 V LVCMOS wide range is applicable to 100 µA drive strength only. The configuration will NOT operate at the equivalent software default drive strength. These values are for Normal Ranges ONLY.*
2. *I_{IL} is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *I_{IH} is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
4. *Currents are measured at 125°C junction temperature.*
5. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-A specification.*
6. *Software default selection highlighted in gray.*

Timing Characteristics

1.2 V DC Core Voltage

Table 2-62 • 3.3 V LVCMOS Wide Range Low Slew
Military-Case Conditions: T_J = 125°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7 V
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	4 mA	Std.	0.80	9.08	0.05	2.18	3.16	0.52	9.08	7.17	3.85	3.40	11.28	9.38	ns
		–1	0.68	7.72	0.05	1.86	2.69	0.44	7.72	6.10	3.28	2.89	9.60	7.98	ns
100 µA	8 mA	Std.	0.80	7.37	0.05	2.18	3.16	0.52	7.37	6.10	4.38	4.35	9.58	8.31	ns
		–1	0.68	6.27	0.05	1.86	2.69	0.44	6.27	5.19	3.73	3.70	8.15	7.07	ns
100 µA	12 mA	Std.	0.80	6.17	0.05	2.18	3.16	0.52	6.17	5.30	4.73	4.94	8.37	7.51	ns
		–1	0.68	5.24	0.05	1.86	2.69	0.44	5.24	4.51	4.03	4.20	7.12	6.38	ns
100 µA	16 mA	Std.	0.80	5.82	0.05	2.18	3.16	0.52	5.82	5.12	4.80	5.11	8.03	7.33	ns
		–1	0.68	4.95	0.05	1.86	2.69	0.44	4.95	4.36	4.09	4.34	6.83	6.23	ns
100 µA	24 mA	Std.	0.80	5.64	0.05	2.18	3.16	0.52	5.64	5.14	4.90	5.72	7.85	7.35	ns
		–1	0.68	4.80	0.05	1.86	2.69	0.44	4.80	4.38	4.17	4.87	6.67	6.25	ns

Notes:

1. *Note that 3.3 V LVCMOS wide range is applicable to 100 µA drive strength only. The configuration will not operate at the equivalent software default drive strength. These values are for normal ranges ONLY.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-63 • 3.3 V LVCMOS Wide Range High Slew
Military-Case Conditions: T_J = 125°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7 V
Applicable to Pro I/O Banks for A3PE600L and A3PE3000L Only

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	4 mA	Std.	0.80	5.00	0.05	2.18	3.16	0.52	5.00	3.77	3.85	3.62	7.21	5.97	ns
		–1	0.68	4.25	0.05	1.86	2.69	0.44	4.25	3.21	3.28	3.08	6.13	5.08	ns
100 µA	8 mA	Std.	0.80	4.07	0.05	2.18	3.16	0.52	4.07	2.98	4.38	4.57	6.27	5.19	ns
		–1	0.68	3.46	0.05	1.86	2.69	0.44	3.46	2.54	3.73	3.89	5.33	4.41	ns
100 µA	12 mA	Std.	0.80	3.54	0.05	2.18	3.16	0.52	3.54	2.60	4.73	5.19	5.74	4.81	ns
		–1	0.68	3.01	0.05	1.86	2.69	0.44	3.01	2.22	4.03	4.42	4.89	4.09	ns
100 µA	16 mA	Std.	0.80	3.45	0.05	2.18	3.16	0.52	3.45	2.54	4.82	5.36	5.66	4.74	ns
		–1	0.68	2.94	0.05	1.86	2.69	0.44	2.94	2.16	4.10	4.56	4.81	4.03	ns
100 µA	24 mA	Std.	0.80	3.49	0.05	2.18	3.16	0.52	3.49	2.44	4.91	5.98	5.69	4.64	ns
		–1	0.68	2.97	0.05	1.86	2.69	0.44	2.97	2.07	4.18	5.08	4.84	3.95	ns

Notes:

1. *Note that 3.3 V LVCMOS wide range is applicable to 100 µA drive strength only. The configuration will not operate at the equivalent software default drive strength. These values are for normal ranges only.*
2. *For specific junction temperature and voltage supply levels, refer to the Table 2-6 on page 2-6 for derating values.*
3. *Software default selection highlighted in gray.*

Table 2-66 • 3.3 V LVCMOS Wide Range Low Slew
Military-Case Conditions: T_J = 125°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V
Applicable to Advanced I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	4 mA	Std.	0.63	9.67	0.05	1.70	0.45	9.67	8.03	4.50	4.18	13.40	11.77	ns
		–1	0.54	8.22	0.04	1.44	0.39	8.22	6.83	3.83	3.55	11.40	10.01	ns
100 µA	6mA	Std.	0.63	8.13	0.05	1.70	0.45	8.13	6.95	5.07	5.17	11.86	10.69	ns
		–1	0.54	6.91	0.04	1.44	0.39	6.91	5.92	4.31	4.40	10.09	9.09	ns
100 µA	8 mA	Std.	0.63	8.13	0.05	1.70	0.45	8.13	6.95	5.07	5.17	11.86	10.69	ns
		–1	0.54	6.91	0.04	1.44	0.39	6.91	5.92	4.31	4.40	10.09	9.09	ns
100 µA	12 mA	Std.	0.63	6.96	0.05	1.70	0.45	6.96	6.15	5.45	5.81	10.70	9.89	ns
		–1	0.54	5.92	0.04	1.44	0.39	5.92	5.24	4.64	4.94	9.10	8.41	ns
100 µA	16 mA	Std.	0.63	6.61	0.05	1.70	0.45	6.61	5.96	5.54	5.97	10.34	9.70	ns
		–1	0.54	5.62	0.04	1.44	0.39	5.62	5.07	4.71	5.08	8.80	8.25	ns

Notes:

1. *Note that 3.3 V LVCMOS wide range is applicable to 100 µA drive strength only. The configuration will not operate at the equivalent software default drive strength. These values are for normal ranges ONLY.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-67 • 3.3 V LVCMOS Wide Range High Slew
Military-Case Conditions: T_J = 125°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V
Applicable to Advanced I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	4 mA	Std.	0.63	5.49	0.05	1.70	0.45	5.49	4.23	4.51	4.44	9.22	7.97	ns
		–1	0.54	4.67	0.04	1.44	0.39	4.57	3.60	3.83	3.78	7.84	6.78	ns
100 µA	6 mA	Std.	0.63	4.56	0.05	1.70	0.45	4.56	3.42	5.08	5.45	8.29	7.15	ns
		–1	0.54	3.88	0.04	1.44	0.39	3.88	2.91	4.32	4.64	7.05	6.08	ns
100 µA	8 mA	Std.	0.63	4.56	0.05	1.70	0.45	4.56	3.42	5.08	5.45	8.29	7.15	ns
		–1	0.54	3.88	0.04	1.44	0.39	3.88	2.91	4.32	4.64	7.05	6.08	ns
100 µA	12 mA	Std.	0.63	4.08	0.05	1.70	0.45	4.08	3.03	5.46	6.09	7.81	6.76	ns
		–1	0.54	3.47	0.04	1.44	0.39	3.47	2.57	4.65	5.18	6.64	5.75	ns
100 µA	16 mA	Std.	0.63	4.00	0.05	1.70	0.45	4.00	2.96	5.55	6.26	7.73	6.69	ns
		–1	0.54	3.40	0.04	1.44	0.39	3.40	2.51	4.72	5.32	6.58	5.69	ns

Notes:

1. *Note that 3.3 V LVCMOS wide range is applicable to 100 µA drive strength only. The configuration will not operate at the equivalent software default drive strength. These values are for normal ranges only.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

1.5 V DC Core Voltage

Table 2-76 • 2.5 V LVCMOS Low Slew
Military-Case Conditions: T_J = 125°C, VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.61	6.73	0.04	1.75	2.26	0.40	6.83	5.71	2.54	1.99	8.30	7.18	ns
	–1	0.52	5.73	0.03	1.49	1.93	0.34	5.81	4.86	2.16	1.69	7.06	6.10	ns
8 mA	Std.	0.61	5.48	0.04	1.75	2.26	0.40	5.56	4.82	2.92	2.71	7.02	6.29	ns
	–1	0.52	4.66	0.03	1.49	1.93	0.34	4.73	4.10	2.48	2.30	5.98	5.35	ns
12 mA	Std.	0.61	4.59	0.04	1.75	2.26	0.40	4.65	4.18	3.18	3.18	6.12	5.65	ns
	–1	0.52	3.91	0.03	1.49	1.93	0.34	3.96	3.56	2.71	2.70	5.20	4.80	ns
16 mA	Std.	0.61	4.32	0.04	1.75	2.26	0.40	4.38	4.04	3.24	3.31	5.84	5.51	ns
	–1	0.52	3.68	0.03	1.49	1.93	0.34	3.72	3.44	2.75	2.81	4.97	4.69	ns
24 mA	Std.	0.61	4.20	0.04	1.75	2.26	0.40	4.26	4.06	3.31	3.76	5.72	5.52	ns
	–1	0.52	3.58	0.03	1.49	1.93	0.34	3.62	3.45	2.82	3.20	4.87	4.70	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-77 • 2.5 V LVCMOS High Slew
Military-Case Conditions: T_J = 125°C, VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.61	3.37	0.04	1.75	2.26	0.40	3.41	3.01	2.54	2.08	4.87	4.48	ns
	–1	0.52	2.87	0.03	1.49	1.93	0.34	2.90	2.56	2.16	1.77	4.14	3.81	ns
8 mA	Std.	0.61	2.74	0.04	1.75	2.26	0.40	2.76	2.29	2.92	2.82	4.23	3.75	ns
	–1	0.52	2.33	0.03	1.49	1.93	0.34	2.35	1.95	2.48	2.40	3.60	3.19	ns
12 mA	Std.	0.61	2.36	0.04	1.75	2.26	0.40	2.38	1.93	3.18	3.27	3.84	3.40	ns
	–1	0.52	2.01	0.03	1.49	1.93	0.34	2.02	1.65	2.71	2.78	3.27	2.89	ns
16 mA	Std.	0.61	2.29	0.04	1.75	2.26	0.40	2.31	1.87	3.24	3.40	3.77	3.33	ns
	–1	0.52	1.95	0.03	1.49	1.93	0.34	1.96	1.59	2.75	2.89	3.21	2.84	ns
24 mA	Std.	0.61	2.31	0.04	1.75	2.26	0.40	2.32	1.78	3.31	3.89	3.79	3.25	ns
	–1	0.52	1.96	0.03	1.49	1.93	0.34	1.98	1.52	2.82	3.31	3.22	2.76	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

Table 2-82 • Minimum and Maximum DC Input and Output Levels Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

1.8 V LVCMOS	VIL		VIH		VOL	VOH	I_{OL}	I_{OH}	I_{OSL}	I_{OSH}	I_{IL}[1]	I_{IH}[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	2	2	9	11	15	15
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4	17	22	15	15
6 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	6	6	35	44	15	15
8 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	8	8	45	51	15	15
12 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	12	12	91	74	15	15
16 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	16	16	91	74	15	15

Notes:

1. *I_{IL} is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *I_{IH} is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 125°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-83 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	V_{OH}	I_{OL}	I_{OH}	I_{OSL}	I_{OSH}	I_{IL}[1]	I_{IH}[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	2	2	9	11	15	15
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	4	4	17	22	15	15
6 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	6	6	35	44	15	15
8 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	8	8	45	51	15	15
12 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	12	12	91	74	15	15
16 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	16	16	91	74	15	15

Notes:

1. *I_{IL} is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *I_{IH} is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 125°C junction temperature.*
5. *Software default selection highlighted in gray.*

Timing Characteristics

1.2 V DC Core Voltage

Table 2-116 • 3.3 V PCI/PCI-X
Military-Case Conditions: T_J = 125°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.80	2.78	0.05	2.71	3.68	0.52	2.83	1.97	3.26	3.59	5.03	4.18	ns
–1	0.68	2.37	0.05	2.31	3.13	0.44	2.40	1.68	2.77	3.06	4.28	3.56	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.5 V DC Core Voltage

Table 2-117 • 3.3 V PCI/PCI-X
Military-Case Conditions: T_J = 125°C, VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.61	2.65	0.04	2.39	3.38	0.40	2.67	1.86	3.10	3.40	4.14	3.33	ns
–1	0.52	2.25	0.03	2.03	2.88	0.34	2.27	1.58	2.64	2.89	3.52	2.83	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-118 • 3.3 V PCI/PCI-X
Military-Case Conditions: T_J = 125°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.63	2.95	0.05	0.95	0.45	3.00	2.15	3.53	3.94	5.46	4.61	ns
–1	0.54	2.51	0.04	0.81	0.39	2.55	1.83	3.00	3.35	4.65	3.92	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

Table 2-119 • 3.3 V PCI/PCI-X
Military-Case Conditions: T_J = 125°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.63	2.54	0.05	0.94	0.45	2.59	1.87	3.07	3.54	5.04	4.33	ns
–1	0.54	2.16	0.04	0.80	0.39	2.20	1.60	2.61	3.01	4.29	3.69	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

Voltage-Referenced I/O Characteristics

3.3 V GTL

Gunning Transceiver Logic is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The V_{CCI} pin should be connected to 3.3 V.

Table 2-120 • Minimum and Maximum DC Input and Output Levels

3.3 V GTL	VIL		VIH		VOL	VOH	I_{OL}	I_{OH}	I_{OSL}	I_{OSH}	I_{IL}[1]	I_{IH}[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
20 mA[5]	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20	268	181	15	15

Notes:

1. *I_{IL} is the input leakage current per I/O pin over recommended operating conditions where –0.3 V < VIN < VIL.*
2. *I_{IH} is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 125°C junction temperature.*
5. *Output drive strength is below JEDEC specification.*

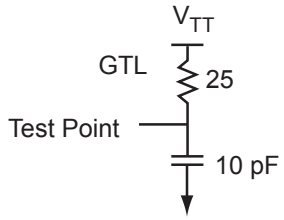

Figure 2-15 • AC Loading

Table 2-121 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.05	VREF + 0.05	0.8	0.8	1.2	10

*Note: *Measuring point = V_{trip}. See Table 2-29 on page 2-25 for a complete table of trip points.*

Timing Characteristics

Table 2-122 • 3.3 V GTL
Military-Case Conditions: T_J = 125°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V, VREF = 0.8 V
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.80	2.05	0.05	2.34	0.52	2.01	2.05	–	–	4.22	4.26	ns
–1	0.68	1.75	0.05	1.99	0.44	1.71	1.75	–	–	3.59	3.62	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

LVPECL

Low-Voltage Positive Emitter-Coupled Logic (LVPECL) is another differential I/O standard. It requires that one data bit be carried through two signal lines. Like LVDS, two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in Figure 2-27. The building blocks of the LVPECL transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVDS implementation because the output standard specifications are different.

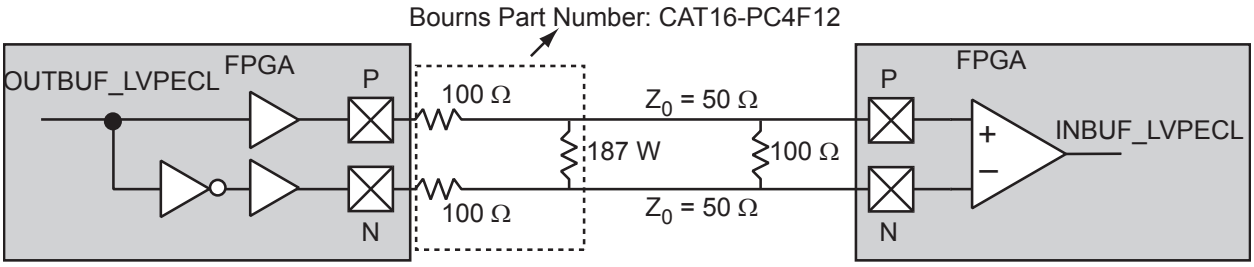

Figure 2-27 • **LVPECL Circuit Diagram and Board-Level Implementation**

Table 2-165 • **Minimum and Maximum DC Input and Output Levels**

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCI	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.3	0	3.6	0	3.9	V
V_{ODIFF}	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
V_{OCM}	Output Common-Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
V_{ICM}	Input Common-Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
V_{IDIFF}	Input Differential Voltage	300		300		300		mV

Table 2-166 • **AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)
1.64	1.94	Cross point

*Note: *Measuring point = V_{trip}. See Table 2-29 on page 2-25 for a complete table of trip points.*

I/O Register Specifications

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

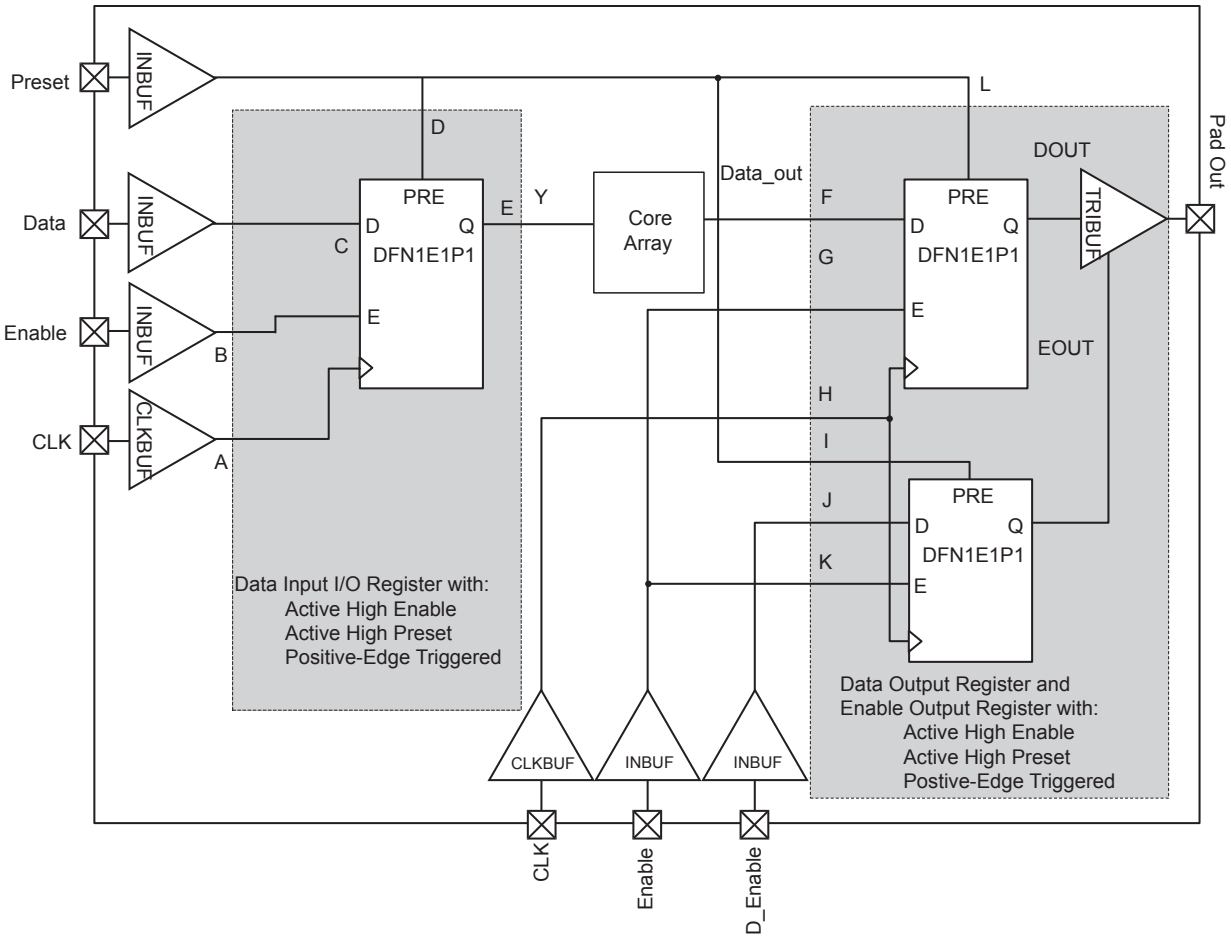

Figure 2-28 • **Timing Model of Registered I/O Buffers with Synchronous Enable and Asynchronous Preset**

Table 2-170 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

* *See Figure 2-28 on page 2-91 for more information.*

Table 2-174 • Input Data Register Propagation Delays
Military-Case Conditions: T_J = 125°C, Worst-Case VCC = 1.425 V for A3P250 and A3P1000

Parameter	Description	–1	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.29	0.34	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.32	0.37	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	0.45	0.53	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.55	0.64	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.55	0.64	ns
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	0.00	ns
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	0.27	0.31	ns
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	0.00	ns
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	0.27	0.31	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.25	0.30	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.25	0.30	ns
$t_{ICKMPWH}$	Clock Minimum Pulse Width HIGH for the Input Data Register	0.41	0.48	ns
$t_{ICKMPWL}$	Clock Minimum Pulse Width LOW for the Input Data Register	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

Table 2-207 • RAM512X18
Military-Case Conditions: T_J = 125°C, VCC = 1.425 V for A3PE600L and A3PE3000L

Parameter	Description	–1	Std.	Units
t_{AS}	Address setup time	0.26	0.31	ns
t_{AH}	Address hold time	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.10	0.11	ns
t_{ENH}	REN, WEN hold time	0.06	0.07	ns
t_{DS}	Input data (WD) setup time	0.19	0.23	ns
t_{DH}	Input data (WD) hold time	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained, WMODE = 0)	2.29	2.69	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	0.95	1.12	ns
t_{C2CRWH}	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge	0.18	0.21	ns
t_{C2CWRH}	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge	0.21	0.25	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow through)	0.98	1.15	ns
	RESET Low to data out Low on RD (pipelined)	0.98	1.15	ns
$t_{REMRSTB}$	RESET removal	0.30	0.36	ns
$t_{RECRSTB}$	RESET recovery	1.59	1.87	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.59	0.67	ns
t_{CYC}	Clock cycle time	5.39	6.20	ns
F_{MAX}	Maximum frequency	185	161	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-213 • FIFO Worst Military-Case Conditions: T_J = 125°C, VCC = 1.425 V for A3P250 (512×8)

Parameter	Description	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	4.52	5.31	ns
t_{ENH}	REN, WEN Hold Time	0.00	0.00	ns
t_{BKS}	BLK Setup Time	1.66	1.95	ns
t_{BKH}	BLK Hold Time	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.22	0.26	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	ns
t_{CKQ1}	Clock HIGH to New Data Valid on RD (flow-through)	2.61	3.06	ns
t_{CKQ2}	Clock HIGH to New Data Valid on RD (pipelined)	1.14	1.34	ns
t_{RCKEF}	RCLK HIGH to Empty Flag Valid	2.07	2.43	ns
t_{WCKFF}	WCLK HIGH to Full Flag Valid	1.96	2.31	ns
t_{CKAF}	Clock HIGH to Almost Empty/Full Flag Valid	7.45	8.76	ns
t_{RSTFG}	RESET LOW to Empty/Full Flag Valid	2.04	2.40	ns
t_{RSTAF}	RESET LOW to Almost Empty/Full Flag Valid	7.38	8.67	ns
t_{RSTBQ}	RESET LOW to Data Out LOW on RD (flow-through)	1.11	1.31	ns
	RESET LOW to Data Out LOW on RD (pipelined)	1.11	1.31	ns
$t_{REMRSTB}$	RESET Removal	0.34	0.40	ns
$t_{RECRSTB}$	RESET Recovery	1.81	2.12	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.26	0.30	ns
t_{CYC}	Clock Cycle Time	3.89	4.57	ns
F_{MAX}	Maximum Frequency for FIFO	257	219	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

FG484	
Pin Number	A3PE600L Function
E18	GBA2/IO36PDB2V0
E19	IO42NDB2V0
E20	GND
E21	NC
E22	NC
F1	NC
F2	IO131NDB7V1
F3	IO131PDB7V1
F4	IO133NDB7V1
F5	IO134NDB7V1
F6	VMV7
F7	VCCPLA
F8	GAC0/IO02NDB0V0
F9	GAC1/IO02PDB0V0
F10	IO15NDB0V2
F11	IO15PDB0V2
F12	IO20PDB1V0
F13	IO25NDB1V0
F14	IO27PDB1V0
F15	GBC0/IO33NDB1V1
F16	VCCPLB
F17	VMV2
F18	IO36NDB2V0
F19	IO42PDB2V0
F20	NC
F21	NC
F22	NC
G1	IO127NDB7V1
G2	IO127PDB7V1
G3	NC
G4	IO128PDB7V1
G5	IO129PDB7V1
G6	GAC2/IO132PDB7V1
G7	VCOMPLA
G8	GNDQ

FG484	
Pin Number	A3PE600L Function
G9	IO09NDB0V1
G10	IO09PDB0V1
G11	IO13PDB0V2
G12	IO21PDB1V0
G13	IO25PDB1V0
G14	IO27NDB1V0
G15	GNDQ
G16	VCOMPLB
G17	GBB2/IO37PDB2V0
G18	IO39PDB2V0
G19	IO39NDB2V0
G20	IO43PDB2V0
G21	IO43NDB2V0
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO128NDB7V1
H5	IO129NDB7V1
H6	IO132NDB7V1
H7	IO130PDB7V1
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO13NDB0V2
H12	IO21NDB1V0
H13	VCCIB1
H14	VCCIB1
H15	VMV1
H16	GBC2/IO38PDB2V0
H17	IO37NDB2V0
H18	IO41NDB2V0
H19	IO41PDB2V0
H20	VCC
H21	NC

FG484	
Pin Number	A3PE600L Function
H22	NC
J1	IO123NDB7V0
J2	IO123PDB7V0
J3	NC
J4	IO124PDB7V0
J5	IO125PDB7V0
J6	IO126PDB7V0
J7	IO130NDB7V1
J8	VCCIB7
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB2
J16	IO38NDB2V0
J17	IO40NDB2V0
J18	IO40PDB2V0
J19	IO45PDB2V1
J20	NC
J21	IO48PDB2V1
J22	IO46PDB2V1
K1	IO121NDB7V0
K2	IO121PDB7V0
K3	NC
K4	IO124NDB7V0
K5	IO125NDB7V0
K6	IO126NDB7V0
K7	GFC1/IO120PPB7V0
K8	VCCIB7
K9	VCC
K10	GND
K11	GND
K12	GND

FG896	
Pin Number	**A3PE3000L Function**
P26	IO111NPB2V3
P27	IO105PDB2V2
P28	IO105NDB2V2
P29	GCC2/IO117PDB3V0
P30	IO117NDB3V0
R1	GFC2/IO270PDB6V4
R2	GFB1/IO274PPB7V0
R3	VCOMPLF
R4	GFA0/IO273NDB6V4
R5	GFB0/IO274NPB7V0
R6	IO271NDB6V4
R7	GFB2/IO271PDB6V4
R8	IO269PDB6V4
R9	IO269NDB6V4
R10	VCCIB7
R11	VCC
R12	GND
R13	GND
R14	GND
R15	GND
R16	GND
R17	GND
R18	GND
R19	GND
R20	VCC
R21	VCCIB2
R22	GCC0/IO112NDB2V3
R23	GCB2/IO116PDB3V0
R24	IO118PDB3V0
R25	IO111PPB2V3
R26	IO122PPB3V1
R27	GCA0/IO114NPB3V0
R28	VCOMPLC
R29	GCB1/IO113PPB2V3
R30	IO115NPB3V0
T1	IO270NDB6V4

Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the "Military ProASIC3/EL Device Status" table on page II, is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

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The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Unmarked (production)

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